



July 8, 1998

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To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 09/086,772 05/29/98

S.M. Jang, M.H. Huang

HARD MASKING METHOD FOR FORMING
PATTERNED OXYGEN CONTAINING PLASMA
ETCHABLE LAYER

Grp. Art Unit: 1763

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

Each of these following Patents and/or Publications have
been mentioned and described in the Specification
of the Subject Patent Application:

U.S. Patent 5,565,384 to Havemamm, "Self-Aligned Via Using Low Permittivity Dielectric", discloses a method where horizontal gaps between the patterned conductors are substantially filled with an organic containing dielectric material.

U.S. Patent 5,654,240 to Lee et al, "Integrated Circuit Fabrication Having Contact Opening", shows an oxide hard mask for metal patterning.

U.S. Patent 5,460,693 to Moslehi, "Dry Microlithography Process", shows oxide hard masks for a fluorinated layer.

U.S. Patent 5,246,883 to Lin et al, "Semiconductor Contact Via Structure And Method", shows a contact via through an IDL layer with different buffer layers.

Sincerely,

A handwritten signature in cursive script that reads "George O. Saile".

George O. Saile, Reg. No. 19572